

PNP Silicon Epitaxial Planar Transistor

B772I-B772D

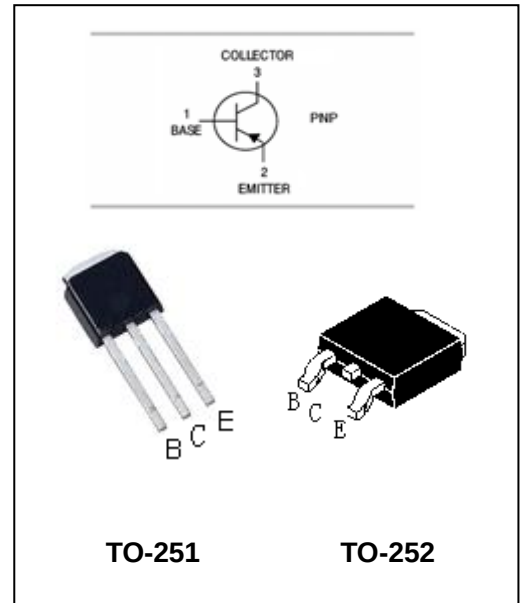
FEATURES

- Low speed switching.
- Low saturation voltage.
- Excellent h_{FE} linearity and high h_{FE} .
- Complementary: D882.

HF

APPLICATIONS

- Audio frequency power amplifier.



Ordering Information

Part Number	Package	Shipping	Marking Code
B772I	TO-251	80 pcs / Tube	B772
B772D	TO-252	80 pcs / Tube or 2500 pcs / Tape & Reel	B772

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient Air	100	°C/W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	°C

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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_B = 0$			-1	μA
Collector cut-off current	I_{CEO}	$V_{CB} = -30V, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6V, I_C = 0$			-1	μA
DC current gain	h_{FE}	$V_{CE} = -2V, I_C = -1A$	60	160	400	
		$V_{CE} = -2V, I_C = -20mA$	30	220		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$		-0.3	-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2A, I_B = -0.2A$		-1.0	-1.5	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -0.1A$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		55		pF

CLASSIFICATION OF h_{FE}

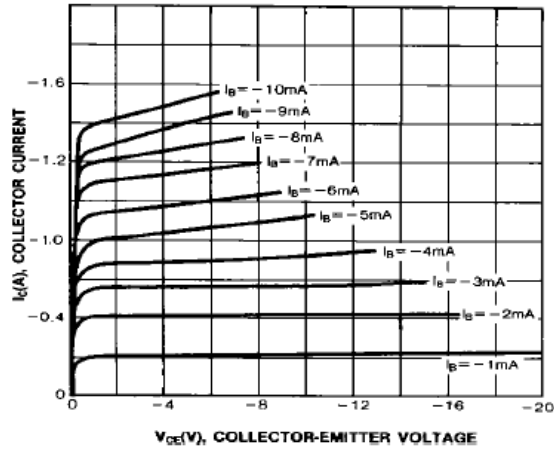
Rank	R	O	Y	G
Range	60-120	100-200	160-320	200-400

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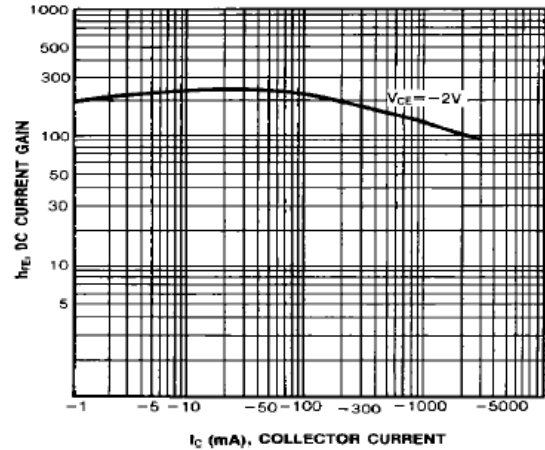
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TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

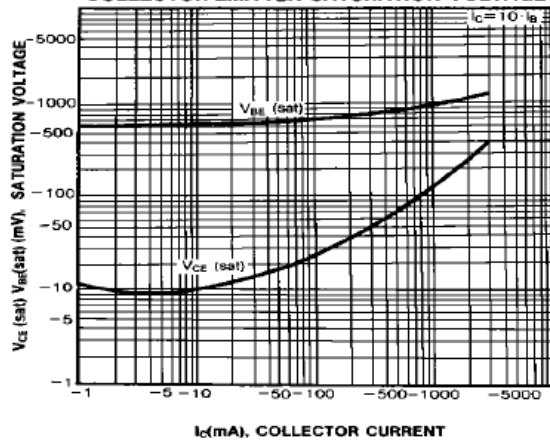
STATIC CHARACTERISTIC



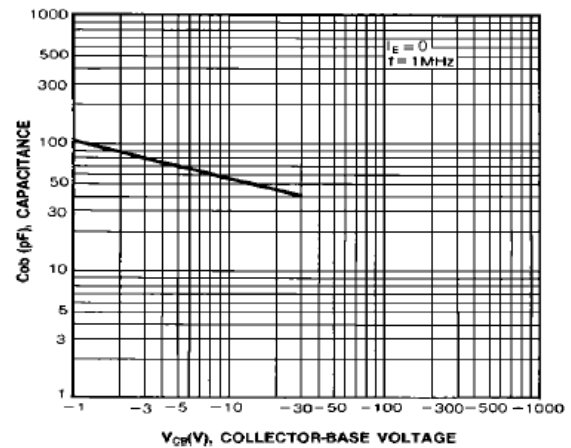
DC CURRENT GAIN



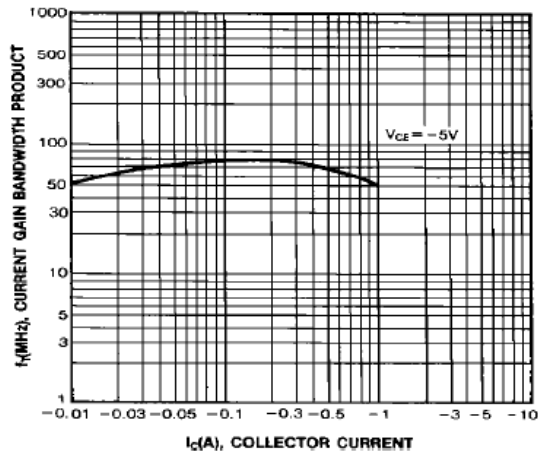
BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



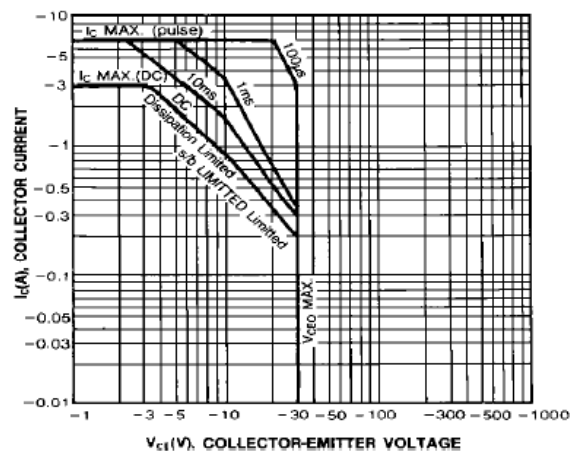
COLLECTOR OUTPUT CAPACITANCE



CURRENT GAIN-BANDWIDTH PRODUCT



SAFE OPERATING AREA



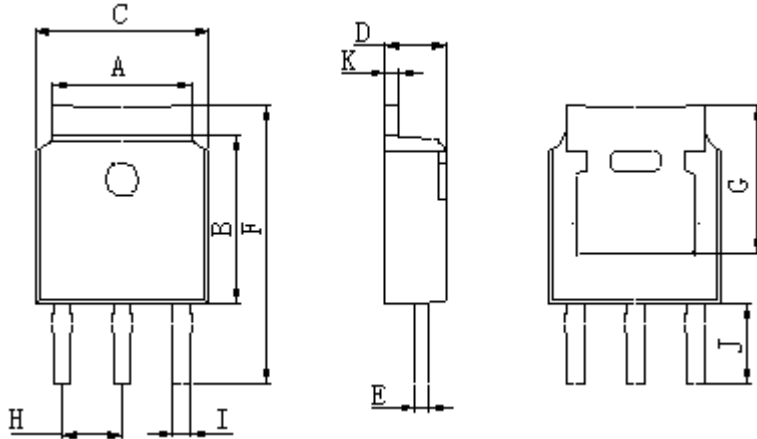
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PACKAGE OUTLINE

Plastic surface mounted package

TO-251

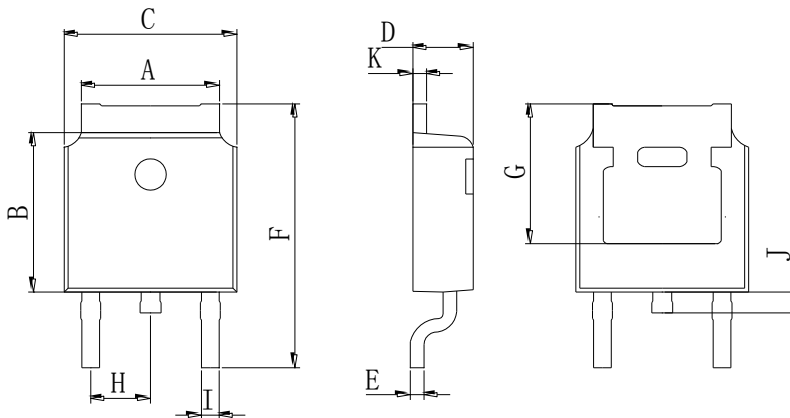


TO-251		
A	5.05	5.65
B	5.80	6.40
C	6.25	6.85
D	2.20	2.40
E	0.40	0.60
F	12.00	12.60
G	5.05	5.65
H	2.10	2.50
I	0.70	0.90
J	4.90	5.50
K	0.40	0.60
All Dimensions in mm		

PACKAGE OUTLINE

Plastic surface mounted package

TO-252

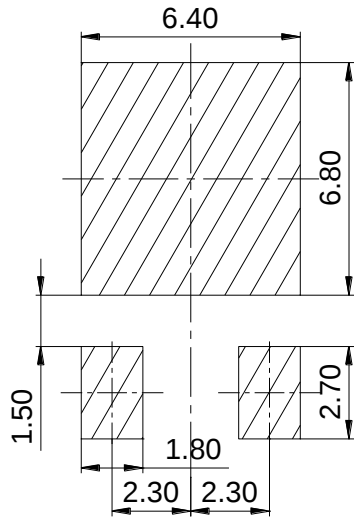


TO-252		
A	5.05	5.65
B	5.80	6.40
C	6.25	6.85
D	2.20	2.40
E	0.40	0.60
F	9.71	10.31
G	5.05	5.65
H	2.10	2.50
I	0.70	0.90
J	0.50	0.70
K	0.40	0.60
All Dimensions in mm		

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SOLDERING FOOTPRINT



Unit: mm